Title	Gate Control, Surface Leakage Currents and Peripheral Charging in AlGaIn/GaN Heterostructure Field Effect Transistors Having Nanometer-Scale Schottky Gates
Author(s)	Kasai, S.; Kotani, J.; Hashizume, T.; Hasegawa, H.
Citation	Journal of Electronic Materials, 35(4), 568-575 https://doi.org/10.1007/s11664-006-0101-5
Issue Date	2006-04
Doc URL	http://hdl.handle.net/2115/10522
Rights	Copyright (c) 2006 The Minerals, Metals & Materials Society (TMS)
Type	article (author version)
Additional Information	There are other files related to this item in HUSCAP. Check the above URL.
File Information	KasaiJEMFigure.pdf (Figures)

[Instructions for use](#)

Figure 1, Kasai et al.

Figure 2, Kasai et al.

Figure 3, Kasai et al.

Figure 4, Kasai et al.

Figure 5, Kasai et al.

Figure 6, Kasai et al.

Figure 7, Kasai et al.

Figure 8, Kasai et al.

Figure 9, Kasai et al.